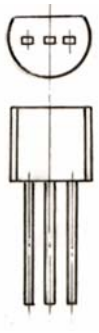
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

S9014 TRANSISTOR (NPN)

TO-92

1. EMITTER
2. BASE
3. COLLECTOR



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FEATURES

- **High total power dissipation.(P_C=0.45W)**
- **High hFE and good linearity**
- **Complementary to S9015**

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	50	V
V_{CEO}	Collector-Emitter Voltage	45	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	0.1	A
P_C	Collector Power Dissipation	0.45	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

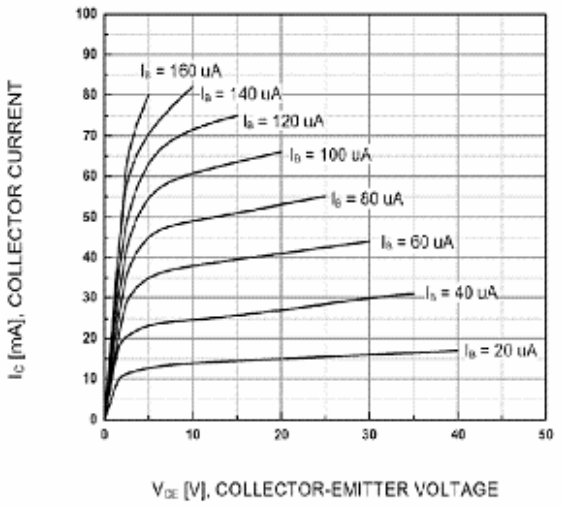
ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=100μA, I_E=0	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= 1mA, I_B=0	45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=50V, I_E=0			0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}=35V, I_B=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 5V, I_C=0			0.1	μA
DC current gain	h_{FE}	V_{CE}=5V, I_C= 1mA	60		1000	
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=100mA, I_B= 5mA			0.3	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=100mA, I_B= 5mA			1	V
Transition frequency	f_T	V_{CE}=5V, I_C= 10mA f=30MHz	150			MHz

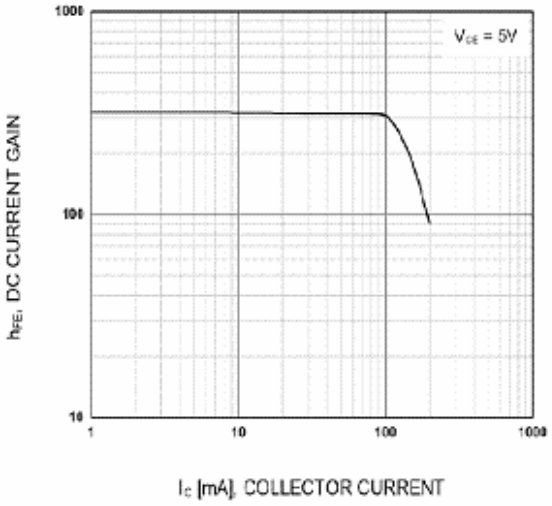
CLASSIFICATION OF $h_{FE(1)}$

Rank	A	B	C	D
Range	60-150	100-300	200-600	400-1000

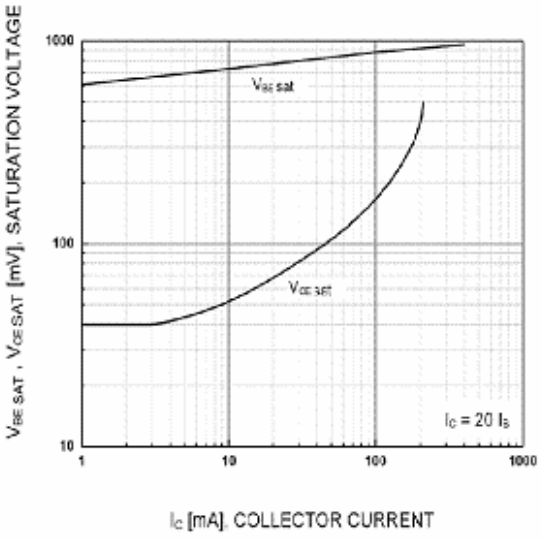
Typical Characteristics S9014



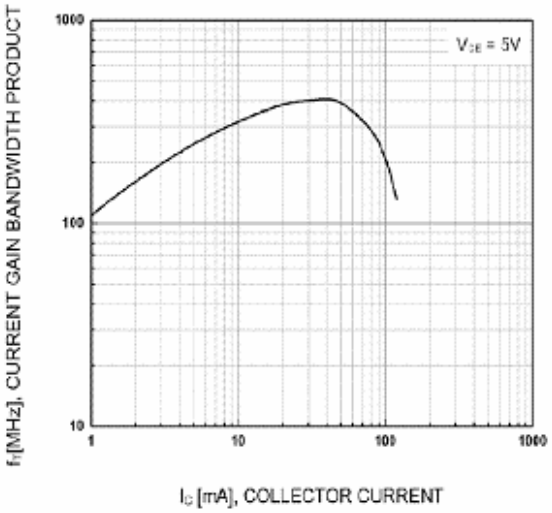
Static Characteristic



DC current Gain



Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage



Current Gain Bandwidth Product